

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising, above a substrate:

a data lines-line extending in a first direction;

a scanning lines-line extending in a second direction which intersects the data lines; line;

a pixel electrodes-electrode and thin film transistors-transistor provided so as to correspond to an intersection regions-region of the data lines-line and the scanning lines; line;

a storage capacitors-capacitor electrically connected to the thin film transistors transistor and the pixel electrodes-electrode, dielectric films which constitute the storage capacitors-capacitor being made of a plurality of at least two layers including different materials and one of the plurality of at least two layers being made of a material having a higher dielectric constant than those that of the other layers; and layer:

a relay layer that electrically connects the pixel electrode and the storage capacitor and that at least partially covers the storage capacitor to shade the storage capacitor from incident light; and

a light shielding layer provided between the data lines-line and the pixel electrodes, electrode, the light shielding layer being formed along the data lines-line and having a width wider than the width of the data lines, line, the light shielding layer being formed to cover the entire data lines-line in plan view, view, the light shielding layer at least partially covering the storage capacitor.

2. (Canceled)

3. (Original) The electro-optical device according to Claim 1, the dielectric films being made of silicon oxide films and silicon nitride films.

4. (Currently Amended) The electro-optical device according to Claim 1, the storage ~~capacitors~~capacitor being formed above ~~a semiconductor~~layer of the thin film ~~transistors~~transistor and below the pixel ~~electrodes~~electrode.

5. (Currently Amended) The electro-optical device according to Claim 1, a planarization process being performed on surfaces of an interlayer insulating film which is positioned beneath the pixel ~~electrodes~~electrode.

6. (Currently Amended) The electro-optical device according to Claim 1, ~~each of~~ the data ~~lines~~line being formed as the same film as one of a pair of electrodes ~~which~~ constitute ~~each of~~ the storage ~~capacitors~~capacitor.

7. (Currently Amended) The electro-optical device according to Claim 1, ~~further~~ comprising: ~~the relay~~layer ~~layer~~ electrically connecting the pixel ~~electrodes~~electrode to one of a pair of electrodes ~~which constitute a corresponding~~of the storage capacitor.

8. (Currently Amended) The electro-optical device according to Claim 7, ~~the~~ light shielding ~~layer and the relay~~layer ~~having a multi-layer structure including a titanium~~ nitride ~~layer formed over an aluminum~~layer, the ~~light shielding~~layer ~~layer~~ being formed as ~~from~~ the same films as the ~~relay~~layer.

9. (Withdrawn-Currently Amended) ~~An~~The electro-optical device comprising, ~~above a substrate~~according to Claim 1,

~~data lines extending in a first direction;~~

~~scanning lines extending in a second direction which intersects the data lines;~~

~~pixel electrodes and thin film transistors provided so as to correspond to~~
~~intersection regions of the data lines and the scanning lines;~~

storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and

shielding layers provided between the data lines and the pixel electrodes, the shielding layers layer being made of transparent conducting materials and formed in a mat shape over the entire surface of the substrate.

10. (Canceled)

11. (Withdrawn-Currently Amended) An The electro-optical device according to Claim 1, comprising, above a substrate:

data lines extending in a first direction;

scanning lines extending in a second direction which intersects the data lines;

pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines;

storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and

the thin film transistors transistor including a semiconductor layers layer having a channel regions region which extend extends in a longitudinal direction and a channel adjacent regions region which extend extends in the longitudinal direction further from the channel regions; region; and

the scanning lines line including a main body parts part extending in a direction intersecting the longitudinal direction and having a gate electrodes electrode of the

thin film ~~transistors-transistor~~ overlapping the channel ~~regions-region~~ in plan view; and view, and

~~—~~ a horizontal ~~protrusions-protrusion~~ protruding from the main body ~~parts-part~~ in the longitudinal direction at ~~sides-a side~~ of the channel adjacent ~~regions-region~~ in plan view.

12. (Currently Amended) The electro-optical device according to Claim 1, the thin film ~~transistors-transistor~~ including a ~~semiconductor layers-layer~~ having a ~~channel regions-region~~ which ~~extend-extends~~ in a longitudinal direction; direction, the electro-optical device further ~~comprising~~: comprising ~~—~~ an upper light-shielding ~~films-film~~ covering at least the ~~channel regions-region~~ of the thin film ~~transistors-transistor~~ from the upper side; and side, ~~—~~ at least a part of the upper light-shielding ~~films-film~~ being formed in a concave shape in the cross section which is perpendicular to the longitudinal direction of the ~~channel regions-region~~ as viewed from the ~~channel regions-region~~.

13. (Withdrawn-Currently Amended) ~~An~~ The electro-optical device according to Claim 1, ~~comprising~~ above a substrate:

~~—~~ data lines extending in a first direction; ~~—~~ scanning lines extending in a second direction which intersects the data lines; ~~—~~ pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines; ~~—~~ storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and ~~—~~ the thin film ~~transistors-transistor~~ including a ~~semiconductor layers-layer~~ having a ~~channel regions-region~~ which ~~extend-extends~~ in the first direction; direction, and

the scanning ~~lines~~-line including a main line portions portion having a gate electrodes electrode of the thin film transistors transistor which face ~~faces~~ the channel regions region with a gate insulating films film interposed therebetween and extending in the second direction which intersects the first direction in plan view; view, and

a surrounding portions portion extending to at least partially surround the semiconductor layers layer from the main line portions portion at positions a position which are ~~is~~ separated from the channel regions region by a predetermined distance in the second direction in plan view.

14. (Currently Amended) ~~An~~ The electro-optical device according to Claim 1, comprising above a substrate:

data lines extending in a first direction;
scanning lines extending in a second direction which intersects the data lines;
pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines;
storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and
the thin film transistors transistor including a semiconductor layers layer having a channel regions region which extend ~~extends~~ in the first direction; direction, and
the scanning ~~lines~~-line including a main line portions portion having a gate electrodes electrode of the thin film transistors transistor which face ~~faces~~ the channel regions region with a gate insulating films film interposed therebetween and extending in the second direction which intersects the first direction in plan view; view, and

—————a vertical protrusions-protrusion protruding downwardly from the main line portions-portion at positions-a position which are-is separated from the channel region by a predetermined distance in the second direction in plan view.

15. (Currently Amended) The electro-optical device according to Claim 14, further comprising: comprising,

—————on the substrate, a lower light-shielding films-film which cover-covers at least the channel regions-region from the lower-side; and side,

—————the vertical protrusions-protrusion contacting the lower light-shielding films-film at a front ends-end thereof.

16. (Withdrawn-Currently Amended) An The electro-optical device according to Claim 1, comprising, above a substrate:

—————data lines extending in a first direction;

—————scanning lines extending in a second direction which intersects the data lines;

—————pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines;

—————storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and

—————the thin film transistors-transistor including a semiconductor layers-layer having a channel regions-region which extend-extends in the first direction; direction, and

—————the scanning lines-line including a main line portions-portion having a gate electrodes-electrode of the thin film transistors-transistor which face-faces the channel regions-region with a gate insulating films-film interposed therebetween and extending in the second direction which intersects the first direction in plan-view; and view,

the main line portions-portion including an inside-groove portions-portion which are-is provided inside grooves-a groove which are-is etched in the substrate and covers at least a part of the channel regions-region from the sides-side.

17. (Withdrawn-Currently Amended) An-The electro-optical device according to Claim 1, comprising, above a substrate:

data lines extending in a first direction; scanning lines extending in a second direction which intersects the data lines; pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines; storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers; and the thin film transistors-transistor including semiconductor layers-layer having a channel regions-region which extend-extends in the first direction, and the scanning lines-line including a main line portions-portion having a gate electrodes-electrode of the thin film transistors-transistor which face-faces the channel regions-region with a gate insulating films-film interposed therebetween and extending in the second direction which intersects the first direction in plan-view, and view, the main line portions-portion including an inside-groove portions-portion which extend-extends in the second direction and are-is provided an inside grooves-groove which are-is etched in the substrate, and an outside-groove portions-portion which extend-extends in the second direction and are-is provided outside the grooves-inside groove.

18. (Currently Amended) An-The electro-optical device according to Claim 1, comprising, above a substrate:

data lines extending in a first direction;
scanning lines extending in a second direction which intersects the data lines;
pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines;
storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers;

a plurality of the pixel electrodes are arranged in a plane and include a first pixel electrode group which is inversely driven at a first period and a second pixel electrode group which is inversely driven at a second period which is complementary to the first period,

at least one of the data lines and/or line or the shielding layers layer including a main line portions portion which are is extended to an upper sides side of the scanning lines line so as to intersect the scanning lines, line, and an overhanging portions portion which overhang along overhangs the scanning lines, line;

a counter electrode which faces the plurality of the pixel electrodes on a counter substrate which is provided opposite to the substrate; and

convex portions being formed on base surfaces of the pixel electrodes on the substrate corresponding to the overhanging portions, the convex portions being regions of gaps between the pixel electrodes, which are adjacent to each other with the scanning lines interposed therebetween in plan view.

19. (Currently Amended) An The electro-optical device according to Claim 1, comprising, above a substrate:

data lines extending in a first direction;
scanning lines extending in a second direction which intersects the data lines;

~~pixel electrodes and thin film transistors provided so as to correspond to intersection regions of the data lines and the scanning lines;~~

~~storage capacitors electrically connected to the thin film transistors and the pixel electrodes, dielectric films which constitute the storage capacitors being made of a plurality of layers including different materials and one of the plurality of layers being made of a material having a higher dielectric constant than those of the other layers;~~

a plurality of the pixel electrodes are arranged in a plane and include a first pixel electrode group which is inversely driven at a first period and a second pixel electrode group which is inversely driven at a second period which is complementary to the first period;

a counter electrode which faces the plurality of the pixel electrodes on a counter substrate which is provided opposite to the substrate; and

convex portions formed in regions of gaps between the pixel electrodes which are adjacent to each other in plan view; and view,

~~the convex portions having gentle step differences which are formed by removing planarization films which are formed in advance on the convex portions by an etching process and causing the surfaces of the convex portions which are exposed after removing to be recessed.~~

20. (Canceled)

21. (Currently Amended) An electronic apparatus including an electro-optical device, the electro-optical device comprising, above a substrate:

a data lines line extending in a first direction;

a scanning lines line extending in a second direction which intersects the data lines; line;

a pixel electrodes-electrode and a thin film transistors-transistor provided so as to correspond to an intersection regions-region of the data lines-line and the scanning lines-line;

line;

a storage capacitors-capacitor electrically connected to the thin film transistors-transistor and the pixel electrodes-electrode,

dielectric films which constitute the storage capacitors-capacitor being made of a plurality of at least two layers including different materials and one of the plurality of the at least two layers being made of a material having a higher dielectric constant than those that of the other layers; layer; and

a relay layer that electrically connects the pixel electrode and the storage capacitor and that at least partially covers the storage capacitor to shade the storage capacitor from incident light; and

a light shielding layer provided between the data lines-line and the pixel electrodes-electrode, the light shielding layer being formed along the data lines-line and having a width wider than the width of the data lines-line, the light shielding layer being formed to cover the entire data lines-line in plan view, the light shielding layer at least partially covering the storage capacitor.

22. (Withdrawn-Currently Amended) The electro-optical device according to Claim 13, the surrounding portion extending to entirely surround the semiconductor layers layer from the main line portions; portion.

23-24. (Canceled)

25. (New) An electro-optical device comprising, above a substrate:

a data line extending in a first direction;

a scanning line extending in a second direction which intersects the data line;

a pixel electrode and thin film transistor provided so as to correspond to an intersection region of the data line and the scanning line;

a storage capacitor electrically connected to the thin film transistor and the pixel electrode; and

a relay layer that electrically connects the pixel electrode and the storage capacitor and that at least partially covers the storage capacitor to shade the storage capacitor from incident light.